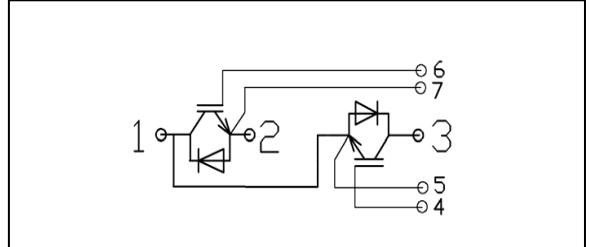


## IGBT MODULE

### Features

- Low  $V_{ce(sat)}$  Non punch
- Ultrafast switching speed
- Low inductance case
- Excellent short circuit ruggedness
- Isolate copper base using DBC technology



### Typical Applications

- UPS
- Electronic welders
- Inductive heating

### Absolute Maximum Ratings of IGBT

$V_{CES}$	Collector to Emitter Voltage		1200	V
$V_{GES}$	Continuous Gate to Emitter Voltage		$\pm 30$	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ\text{C}$	600	A
		$T_C = 100^\circ\text{C}$	300	
$I_{CM}$	Pulse Collector Current	$T_J = 150^\circ\text{C}$	600	A
$P_D$	Maximum Power Dissipation (IGBT)	$T_C = 25^\circ\text{C}$ , $T_J = 150^\circ\text{C}$	1315	W
$t_{sc}$	Short Circuit Withstand Time		> 10	$\mu\text{s}$
$T_J$	Maximum IGBT Junction Temperature		150	$^\circ\text{C}$
$T_{JOP}$	Maximum Operating Junction Temperature Range		-40 to +150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range		-40 to +125	$^\circ\text{C}$

### Absolute Maximum Ratings of Freewheeling Diode

$V_{RRM}$	Repetitive Peak Reverse Voltage	Preliminary Data	1200	V
$I_F$	Diode Continuous Forward Current	$T_C = 25^\circ\text{C}$	600	A
		$T_C = 100^\circ\text{C}$	300	
$I_{FM}$	Diode Maximum Forward Current		600	A

## Electrical Characteristics of IGBT at $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter	Test Conditions	Min	Typ	Max	Unit	
$BV_{CES}$	Collector to Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	1200		V	
$I_{CES}$	Collector to Emitter Leakage Current	$V_{GE} = 0V, V_{CE} = V_{CES}$		5	mA	
$I_{GES}$	Gate to Emitter Leakage Current	$V_{GE} = \pm 30V, V_{CE} = 0V$		400	nA	
$V_{GE(th)}$	Gate Threshold Voltage	$I_C = 1mA, V_{CE} = V_{GE}$	4.5	5.7	V	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage (Module Level)	$I_C = 300A, V_{GE} = 15V$	$T_J = 25^\circ\text{C}$	3.00	3.20	V
			$T_J = 125^\circ\text{C}$	3.60		

## Switching Characteristics of IGBT

Parameter	Test Conditions	Min	Typ	Max	Unit	
$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 600V, I_C = 300A, R_G = 3.3\Omega, V_{GE} = \pm 15V, \text{Inductive Load}$	$T_J = 25^\circ\text{C}$	130		ns
			$T_J = 125^\circ\text{C}$	140		
$t_r$	Turn-on Rise Time	$V_{CC} = 600V, I_C = 300A, R_G = 3.3\Omega, V_{GE} = \pm 15V, \text{Inductive Load}$	$T_J = 25^\circ\text{C}$	105		ns
			$T_J = 125^\circ\text{C}$	110		
$t_{d(off)}$	Turn-off Delay Time	$V_{CC} = 600V, I_C = 300A, R_G = 3.3\Omega, V_{GE} = \pm 15V, \text{Inductive Load}$	$T_J = 25^\circ\text{C}$	820		ns
			$T_J = 125^\circ\text{C}$	890		
$t_f$	Turn-off Fall Time	$V_{CC} = 600V, I_C = 300A, R_G = 3.3\Omega, V_{GE} = \pm 15V, \text{Inductive Load}$	$T_J = 25^\circ\text{C}$	110		ns
			$T_J = 125^\circ\text{C}$	130		
$E_{on}$	Turn-on Switching Loss	$V_{CC} = 600V, I_C = 300A, R_G = 3.3\Omega, V_{GE} = \pm 15V, \text{Inductive Load}$	$T_J = 25^\circ\text{C}$	11.5		mJ
			$T_J = 125^\circ\text{C}$	15.5		
$E_{off}$	Turn-off Switching Loss	$V_{CC} = 600V, I_C = 300A, R_G = 3.3\Omega, V_{GE} = \pm 15V, \text{Inductive Load}$	$T_J = 25^\circ\text{C}$	22.5		mJ
			$T_J = 125^\circ\text{C}$	26.0		
$Q_g$	Total Gate Charge	$V_{CC} = 600V, I_C = 300A, R_G = 3.3\Omega, V_{GE} = \pm 15V, \text{Inductive Load}$	$T_J = 25^\circ\text{C}$	2550		nC
$R_{gint}$	Integrated gate resistor	$f = 1M; V_{pp} = 1V$	$T_J = 25^\circ\text{C}$	2.5		$\Omega$
$C_{ies}$	Input Capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$	$T_J = 25^\circ\text{C}$	25		nF
$C_{oes}$	Output Capacitance		$T_J = 25^\circ\text{C}$	3.5		
$C_{res}$	Reverse Transfer Capacitance		$T_J = 25^\circ\text{C}$	2.0		
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (IGBT)				0.095	$^\circ\text{C/W}$

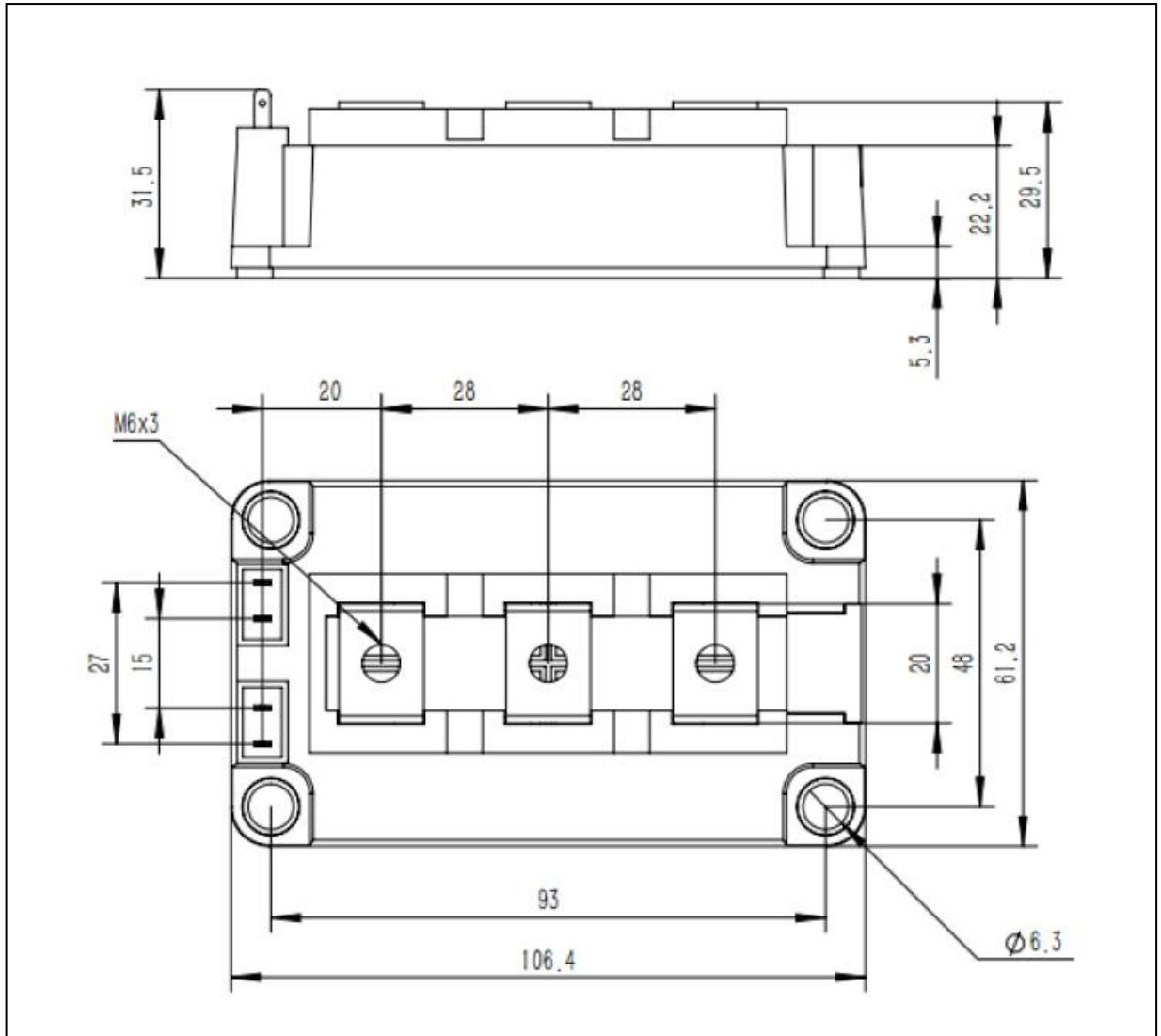
**Electrical and Switching Characteristics of Freewheeling Diode**

V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 300A , V <sub>GE</sub> = 0V	T <sub>J</sub> = 25°C	1.90	2.20	V	
			T <sub>J</sub> = 125°C	1.90			
t <sub>rr</sub>	Diode Reverse Recovery Time	I <sub>F</sub> = 300A, di/dt=2780A/ s, V <sub>rr</sub> = 600V,	T <sub>J</sub> = 25°C	200		ns	
			T <sub>J</sub> = 125°C	300			
I <sub>rr</sub>	Diode Peak Reverse Recovery Current		T <sub>J</sub> = 25°C	230		A	
			T <sub>J</sub> = 125°C	290			
Q <sub>rr</sub>	Diode Reverse Recovery Charge		T <sub>J</sub> = 25°C	27.50		nC	
			T <sub>J</sub> = 125°C	46.50			
E <sub>rr</sub>	Diode Reverse Recovery Energy		T <sub>J</sub> = 25°C	10.00		mJ	
			T <sub>J</sub> = 125°C	17.50			
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case (Diode)				0.115	°C/W	

**Module Characteristics**

Parameter		Min.	Typ.	Max.	Unit
V <sub>iso</sub>	Isolation Voltage (All Terminals Shorted),f = 50Hz, 1minute	2500			V
R <sub>cs</sub>	Case-To-Sink(Conductive Grease Applied)		0.1		°C/W
M	Power Terminals Screw: M6	3.0		5.0	N·m
M	Mounting Screw: M6	4.0		6.0	N·m
G	Weight		315		g

Outline in MM



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